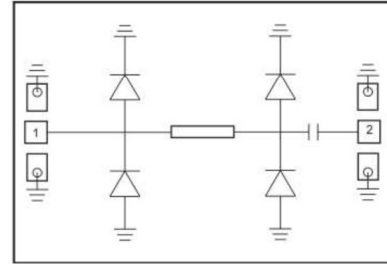


Performance

- Frequency: 1-6GHz
- Insertion loss: 0.5dB
- Limit Level: 16dBm
- Withstand Power: 40W (1-2GHz, CW)
100W (Pulsed, PW=3ms, DC=30%)
- Chip size: 1.80*1.30*0.1mm

Function Diagram

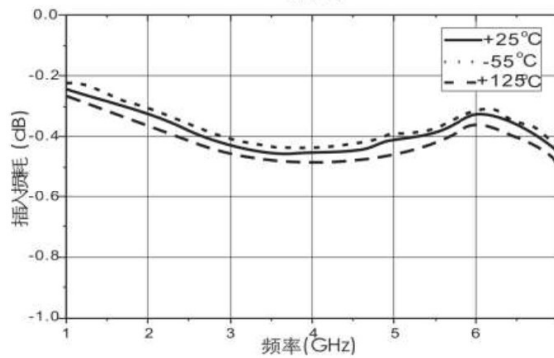


Electrical Specifications (Ta=+25°C, 50Ω system)

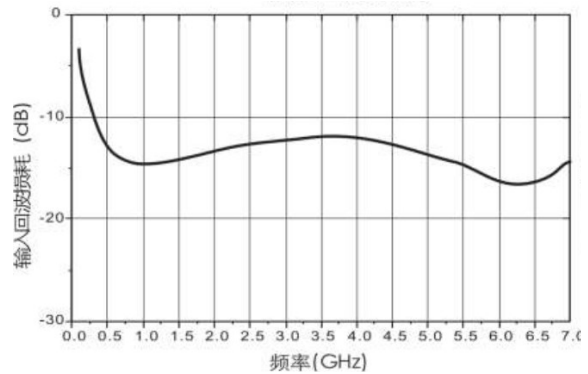
Parameter	Min	Typical	Max	Unit
Frequency Range		1-6		GHz
Insertion Loss	-	0.4	0.6	dB
Return loss	12	15	-	dB
Limit Level	-	16	-	dBm

Test Curves

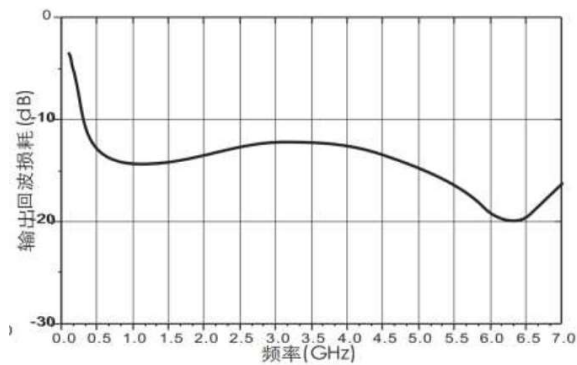
Insertion loss vs. Freq



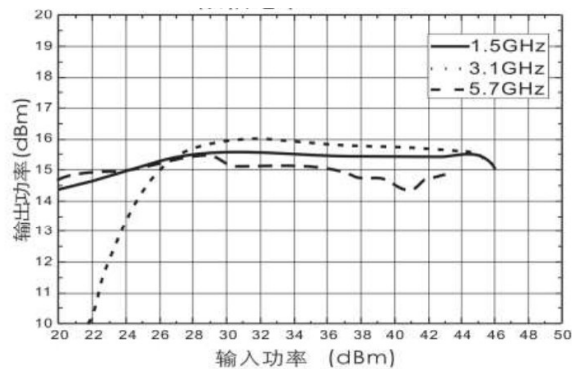
Input Return loss vs. Freq



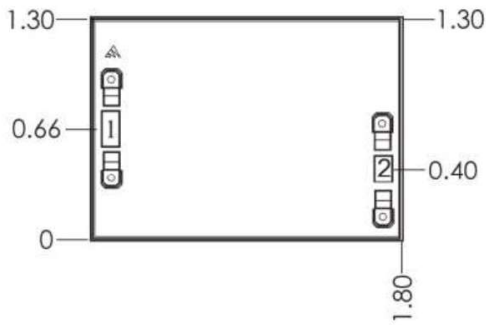
Output Return loss vs. Freq



Limit Level @ 3.1GHz



Outline Size



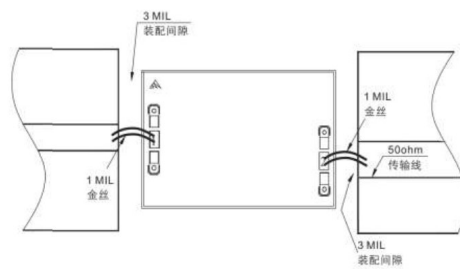
Note:

1. Unit: um
2. Bottom side is gold plated
3. Bottom side is GND
4. Bonding pads is gold plated, size: 0.15*0.1mm
5. Don't bonding on thru holds
6. Tolerance: $\pm 0.05\text{mm}$

Bonding Pads Definition

Number	Symbol	Description
1	RFin	RF input port, 50ohm
2	RFout	RF output port, 50 ohm
-	GND	Bottom must be GND

Application



Absolute Max Ratings

Max Input Power	100W (Pulsed, PW=3ms, DC=30%)
Storage Temperature	-65 ~ +150°C
Operating Temperature	-55 ~ +125°C

Note: For high power application, assemble with Eutectic sintering.



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS